



Description

JMT N-channel MOSFET

Features

- $V_{DS}=60V$, $I_D=0.3A$
- $R_{DS(ON)} < 3.6\Omega$ @ $V_{GS} = 5V$
 $R_{DS(ON)} < 2.8\Omega$ @ $V_{GS} = 10V$
- ESD Rating HBM 2.3KV
- High Power and Current Handling Capability
- Lead Free Product is Acquired
- Surface Mount Package

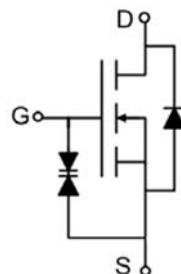
Application

- Battery Operated Systems
- Direct logic-level Interface: TTL/CMOS
- Solid-State Relays

Package



SOT-23



Absolute Maximum Ratings ($T_C=25^\circ C$ unless otherwise specified)

Symbol	Parameter		Max.	Units
V_{DSS}	Drain-Source Voltage		60	V
V_{GSS}	Gate-Source Voltage		± 20	V
I_D	Continuous Drain Current	$T_C = 25^\circ C$	0.3	A
		$T_C = 100^\circ C$	0.24	
I_{DM}	Pulsed Drain Current ^{note1}		0.9	A
P_D	Power Dissipation	$T_C = 25^\circ C$	0.35	W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient		350	$^\circ C/W$
T_J , T_{STG}	Operating and Storage Temperature Range		-55 to +150	$^\circ C$



Electrical Characteristics ($T_C=25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristic						
$V_{(\text{BR})\text{DSS}}$	Drain-Source Breakdown Voltage	$V_{GS}=0\text{V}, I_D=250\mu\text{A}$	60	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=60\text{V}, V_{GS}=0\text{V}$,	-	-	1	μA
I_{GSS}	Gate to Body Leakage Current	$V_{DS}=0\text{V}, V_{GS}=\pm 20\text{V}$	-	-	± 10	μA
On Characteristics						
$V_{GS(\text{th})}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu\text{A}$	1.1	-	2.4	V
$R_{DS(\text{on})}$ note2	Static Drain-Source on-Resistance	$V_{GS}=5\text{V}, I_D=0.4\text{A}$	-	-	3.6	Ω
		$V_{GS}=10\text{V}, I_D=0.5\text{A}$	-	-	2.8	
g_{FS}	Forward Transconductance	$V_{DS}=10\text{V}, I_D=0.2\text{A}$	0.1	-	-	S
Dynamic Characteristics						
C_{iss}	Input Capacitance	$V_{DS}=25\text{V}, V_{GS}=0\text{V}, f=1.0\text{MHz}$	-	21	-	pF
C_{oss}	Output Capacitance		-	11	-	pF
C_{rss}	Reverse Transfer Capacitance		-	4.2	-	pF
Q_g	Total Gate Charge	$V_{DS}=10\text{V}, I_D=0.3\text{A}, V_{GS}=4.5\text{V}$	-	1.7	-	nC
Q_{gs}	Gate-Source Charge		-	0.65	-	nC
Q_{gd}	Gate-Drain("Miller") Charge		-	0.8	-	nC
Switching Characteristics						
$t_{d(on)}$	Turn-on Delay Time	$V_{DD}=30\text{V}, I_D=0.2\text{A}, R_{GEN}=10\Omega, V_{GS}=10\text{V}$	-	10	15	ns
t_r	Turn-on Rise Time		-	50	85	ns
$t_{d(off)}$	Turn-off Delay Time		-	17	45	ns
t_f	Turn-off Fall Time		-	10	20	ns
Drain-Source Diode Characteristics and Maximum Ratings						
I_s	Maximum Continuous Drain to Source Diode Forward Current	-	-	0.3	A	
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current	-	-	0.9	A	
V_{SD}	Drain to Source Diode Forward Voltage	$V_{GS}=0\text{V}, I_s=0.2\text{A}$	-	0.75	1.2	V

Notes:1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

2. Pulse Test: Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 2\%$

Typical Performance Characteristics

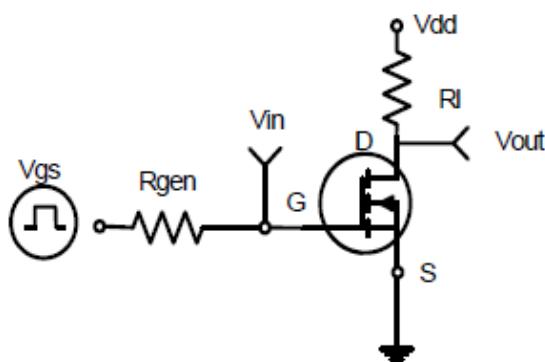


Figure1:Switching Test Circuit

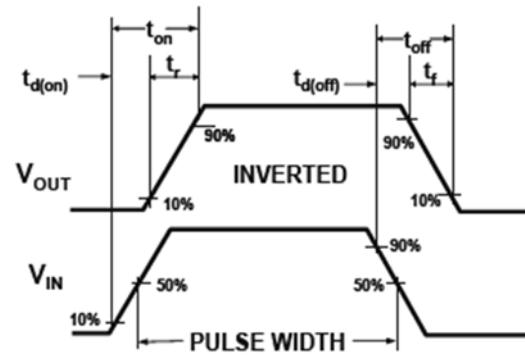
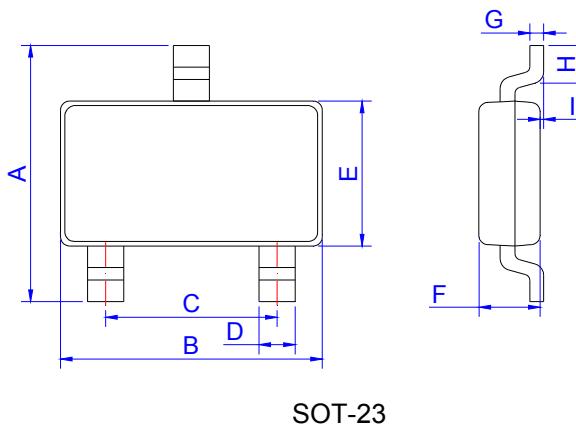


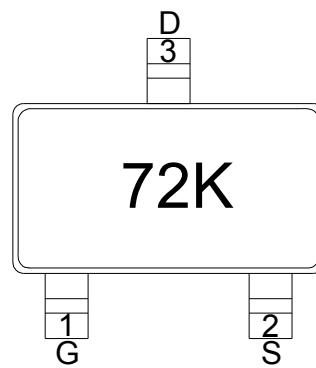
Figure2:Switching Waveforms

Package Mechanical Data



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.30	2.40	2.50	0.091	0.095	0.098
B	2.80	2.90	3.00	0.110	0.114	0.118
C	1.90 REF			0.075 REF		
D	0.35	0.40	0.45	0.014	0.016	0.018
E	1.20	1.30	1.40	0.047	0.051	0.055
F	0.90	1.00	1.10	0.035	0.039	0.043
G		0.10	0.15		0.004	0.006
H	0.20				0.008	
I	0			0.10	0	0.004

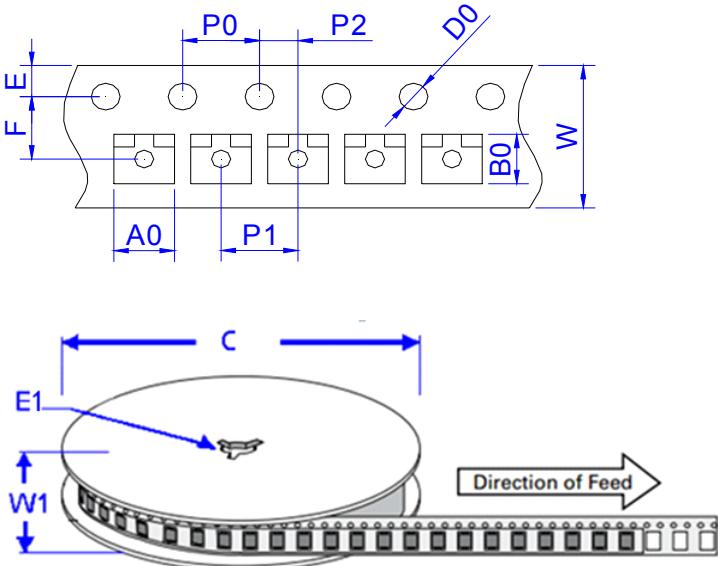
Marking



72K: Device Code



Package Information-SOT-23



Ref.	Dimensions	
	Millimeters	Inches
A0	3.15 ± 0.3	0.124 ± 0.012
B0	2.77 ± 0.3	0.109 ± 0.012
C	178	7.0
D0	1.50±0.1	0.059 ± 0.004
E	1.75 ± 0.2	0.069 ± 0.008
E1	13.3±0.3	0.524± 0.012
F	3.5 ± 0.2	0.138 ± 0.008
P0	4.00 ± 0.2	0.157 ± 0.008
P1	4.00 ± 0.2	0.157 ± 0.008
P2	2.00 ± 0.2	0.079 ± 0.008
W	8.00 ± 0.2	0.315 ± 0.008
W1	11.5±1.0	0.453 ± 0.039

Ordering Information-SOT-23

OUTLINE	PACKAGE TYPE	QUANTITY REEL	DESCRIPTION
TAPING	SOT-23	3,000pcs	7 inch reel pack

Information furnished in this document is believed to be accurate and reliable. However, Jiangsu JieJie Microelectronics Co.,Ltd assumes no responsibility for the consequences of use without consideration for such information nor use beyond it.

Information mentioned in this document is subject to change without notice, apart from that when an agreement is signed, Jiangsu JieJie complies with the agreement.

Products and information provided in this document have no infringement of patents. Jiangsu JieJie assumes no responsibility for any infringement of other rights of third parties which may result from the use of such products and information.

This document is the second version which is made in 11-June-2018. This document supersedes and replaces all information previously supplied.

 is a registered trademark of Jiangsu JieJie Microelectronics Co.,Ltd.
Copyright ©2018 Jiangsu JieJie Microelectronics Co.,Ltd. Printed All rights reserved.

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for MOSFET category:

Click to view products by JieJie manufacturer:

Other Similar products are found below :

[614233C](#) [648584F](#) [MCH3443-TL-E](#) [MCH6422-TL-E](#) [FDPF9N50NZ](#) [FW216A-TL-2W](#) [FW231A-TL-E](#) [APT5010JVR](#) [NTNS3A92PZT5G](#)
[IRF100S201](#) [JANTX2N5237](#) [2SK2464-TL-E](#) [2SK3818-DL-E](#) [FCA20N60_F109](#) [FDZ595PZ](#) [STD6600NT4G](#) [FSS804-TL-E](#) [2SJ277-DL-E](#)
[2SK1691-DL-E](#) [2SK2545\(Q,T\)](#) [D2294UK](#) [405094E](#) [423220D](#) [MCH6646-TL-E](#) [TPCC8103,L1Q\(CM](#) [367-8430-0972-503](#) [VN1206L](#)
[424134F](#) [026935X](#) [051075F](#) [SBVS138LT1G](#) [614234A](#) [715780A](#) [NTNS3166NZT5G](#) [751625C](#) [873612G](#) [IRF7380TRHR](#)
[IPS70R2K0CEAKMA1](#) [RJK60S3DPP-E0#T2](#) [RJK60S5DPK-M0#T0](#) [APT5010JVFR](#) [APT12031JFLL](#) [APT12040JVR](#) [DMN3404LQ-7](#)
[NTE6400](#) [JANTX2N6796U](#) [JANTX2N6784U](#) [JANTXV2N5416U4](#) [SQM110N05-06L-GE3](#) [SIHF35N60E-GE3](#)